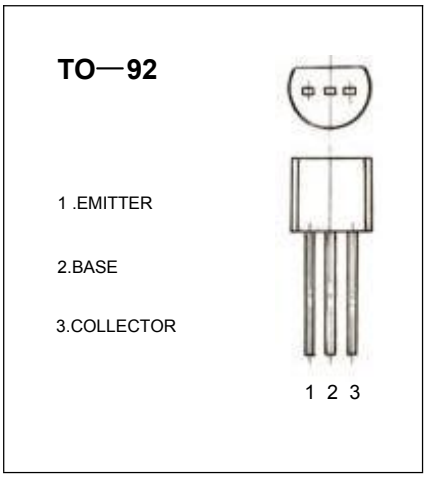
TO-92 Plastic-Encapsulate Transistors

KSP56 TRANSISTOR（ NPN ）



FEATURES

Power dissipation

P_{CM}: 0.625 W（Tamb=25℃）

Collector current

I_{CM}: 0.5 A

Collector-base voltage

$V_{(BR)CBO}$: 80 V

Operating and storage junction temperature range

T_J，T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C=1mA, I_B=0	80			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E=100μA, I_C=0	4.0			V
Collector cut-off current	I_{CBO}	V_{CB}=80V , I_E=0			0.1	μA
Collector cut-off current	I_{CBO}	V_{CE}=60V , I_B=0			0.1	μA
DC current gain(note)	H_{FE}（1）	V_{CE}=1V, I_C=10mA	50			
DC current gain(note)	H_{FE}（2）	V_{CE}=1V, I_C=100mA	50			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=100mA, I_B=10mA			0.25	V
Base-emitter voltage	V_{BE}	V_{CE}=1V , I_C=10mA			1.2	V
Current Gain Bandwidth Product	f_T	V_{CE}=2V, I_C=4mA f=100MHz	50			MHz

CLASSIFICATION OF HFE

Rank	1	2
Range	50-100	100-200